



ZXMN2F34MA

20V DFN2X2 N-channel enhancement mode MOSFET

Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.060 @ $V_{GS} = 4.5V$	5.1
	0.120 @ $V_{GS} = 2.5V$	3.6

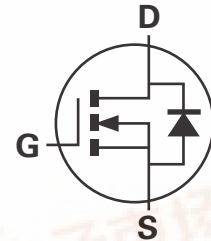


Description

This new generation Trench MOSFET from Zetex features low on-resistance achievable with low (2.5V) gate drive. The 2mm x 2mm DFN package provides superior thermal performance versus alternative leaded devices

Features

- Low on-resistance
- Superior thermal performance (versus to SOT23)
- 2.5V gate drive capability
- DFN 2x2 package

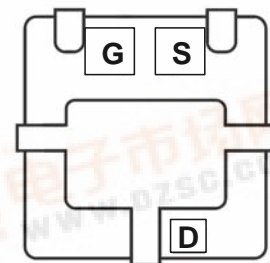


Applications

- Buck/Boost DC-DC Converters
- Motor Control
- LED Lighting

Ordering information

DEVICE	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN2F34MATA	7	8	3000



Device marking

1M4

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Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain source voltage	V_{DSS}	20	V
Gate source voltage	V_{GS}	± 12	V
Continuous Drain Current @ $V_{GS}=4.5$; $T_A=25^{\circ}\text{C}^{(b)}$ @ $V_{GS}=4.5$; $T_A=70^{\circ}\text{C}^{(b)}$ @ $V_{GS}=4.5$; $T_A=25^{\circ}\text{C}^{(a)}$	I_D	5.1 4.1 4.0	A A A
Pulsed drain current ^(c)	I_{DM}	19	A
Continuous source current (body diode) ^(b)	I_S	2.2	A
Pulsed source current (body diode) ^(c)	I_{SM}	19	A
Power dissipation at $T_A=25^{\circ}\text{C}^{(a)}$ Linear derating factor	P_D	1.35 10.8	W mW/ $^{\circ}\text{C}$
Power dissipation at $T_A=25^{\circ}\text{C}^{(b)}$ Linear derating factor	P_D	2.2 17.8	W mW/ $^{\circ}\text{C}$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	92.5	$^{\circ}\text{C/W}$
Junction to ambient ^(b)	$R_{\theta JA}$	56	$^{\circ}\text{C/W}$
Junction to lead ^(d)	$R_{\theta JL}$	19	$^{\circ}\text{C/W}$

NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

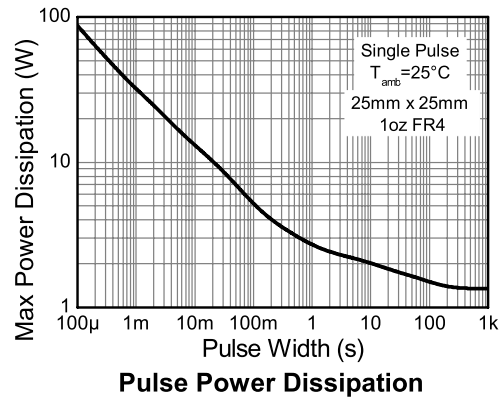
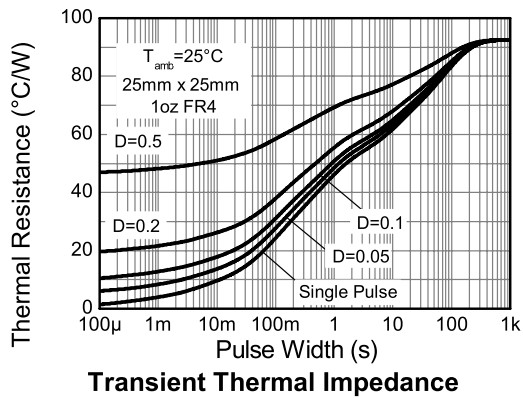
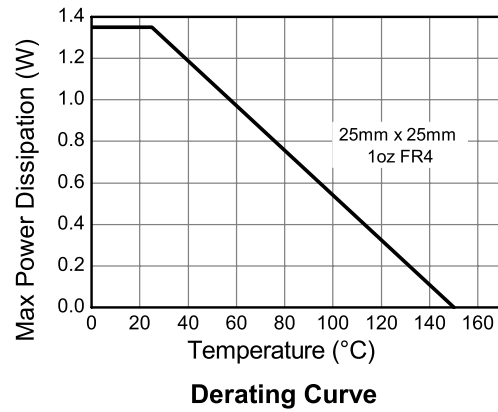
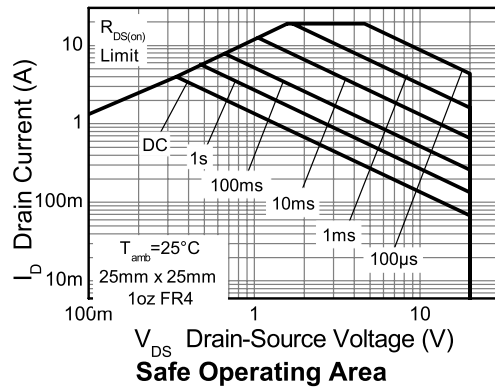
(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

(d) Thermal resistance from junction to solder-point (at end of drain lead).

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Thermal characteristics



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Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	20			V	I _D = 250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 20V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±12V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	0.5	0.8	1.5	V	I _D = 250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance (*)	R _{DS(on)}			0.060 0.120	Ω Ω	V _{GS} = 4.5V, I _D = 2.5A V _{GS} = 2.5V, I _D = 1.0A
Forward Transconductance(*) (†)	g _{fs}		7.5		S	V _{DS} = 10V, I _D = 2.5A
Dynamic (†)						
Input Capacitance	C _{iss}		277		pF	V _{DS} = 10V, V _{GS} =0V f=1MHz
Output Capacitance	C _{oss}		65		pF	
Reverse Transfer Capacitance	C _{rss}		35		pF	
Switching (‡)(†)						
Turn-On-Delay Time	t _{d(on)}		2.65		ns	V _{DD} = 10V, V _{GS} = 4.5V I _D = 1A R _G ≈ 6.0Ω
Rise Time	t _r		4.2		ns	
Turn-Off Delay Time	t _{d(off)}		9.9		ns	
Fall Time	t _f		5.1		ns	
Total Gate Charge	Q _g		2.8		nC	V _{DS} = 10V, V _{GS} = 4.5V I _D = 2.5A
Gate-Source Charge	Q _{gs}		0.61		nC	
Gate Drain Charge	Q _{gd}		0.63		nC	
Source-drain diode						
Diode Forward Voltage(*)	V _{SD}		0.73	1.2	V	I _S = 1.25A, V _{GS} =0V

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

(†) For design aid only, not subject to production testing.

(‡) Switching characteristics are independent of operating junction temperature.

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Typical characteristics

Fig1. I_D - V_{DS}

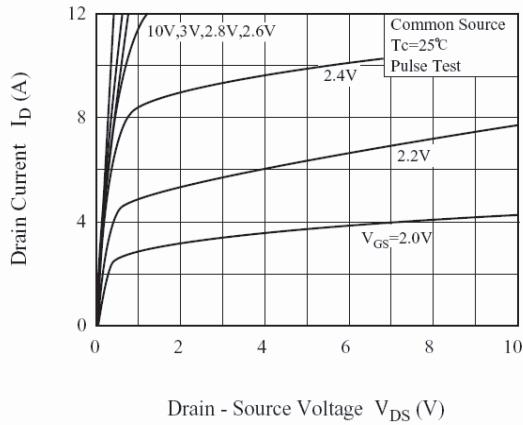


Fig2. $R_{DS(on)}$ - I_D

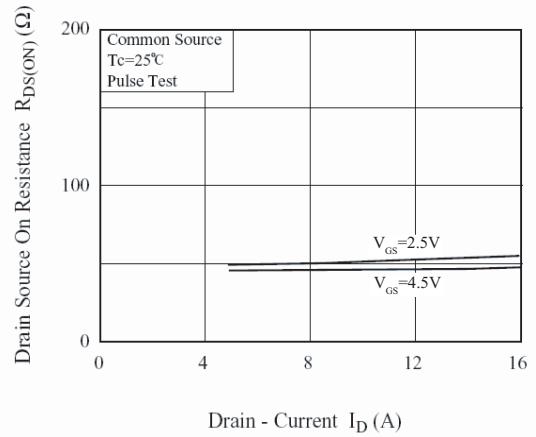


Fig3. I_D - V_{GS}

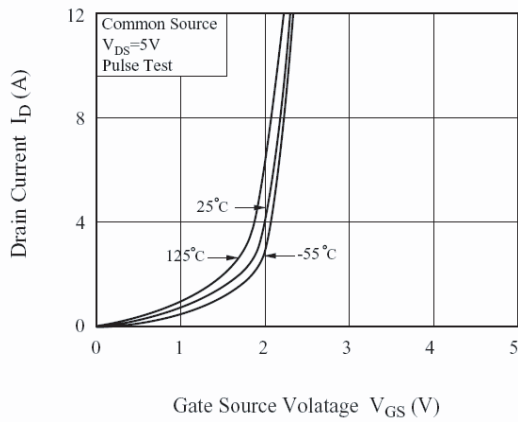


Fig4. $R_{DS(on)}$ - T_j

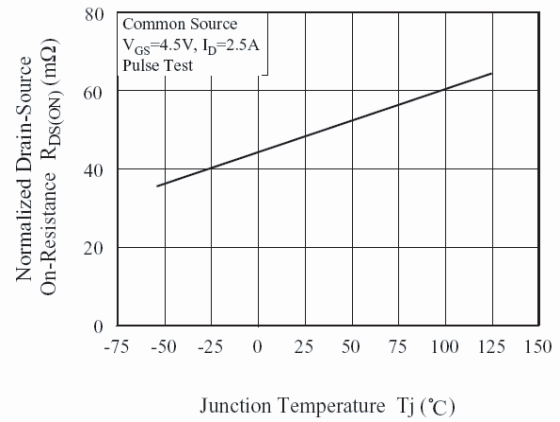


Fig5. V_{th} - T_j

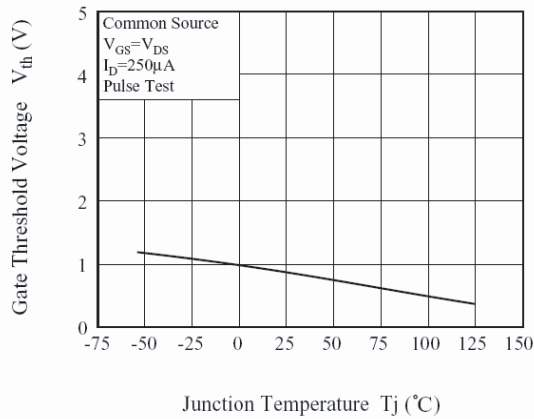
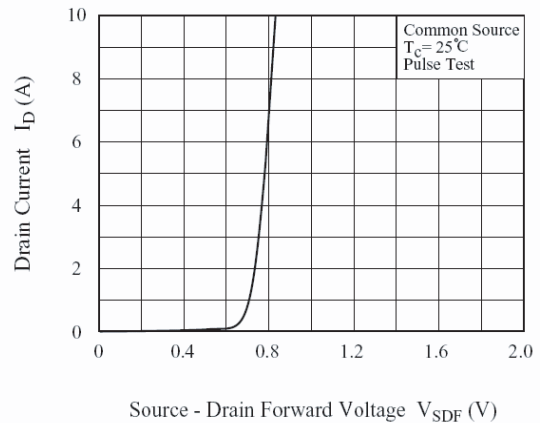
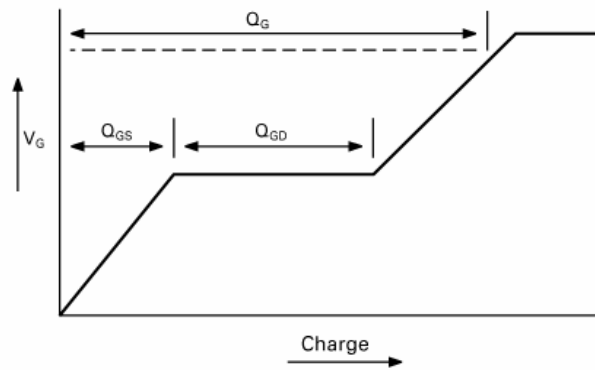


Fig6. I_S - V_{SDF}

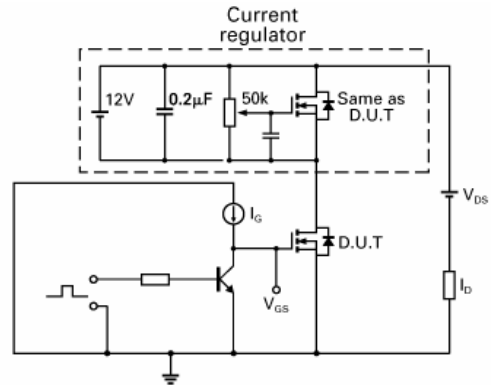


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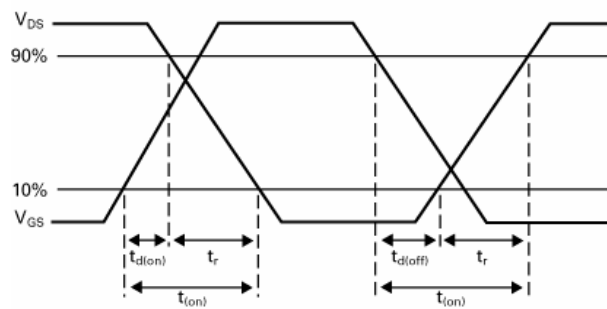
Test circuits



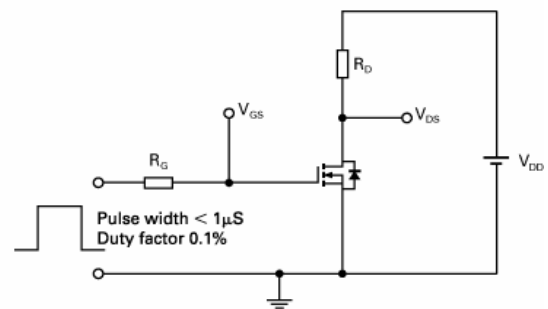
Basic gate charge waveform



Gate charge test circuit



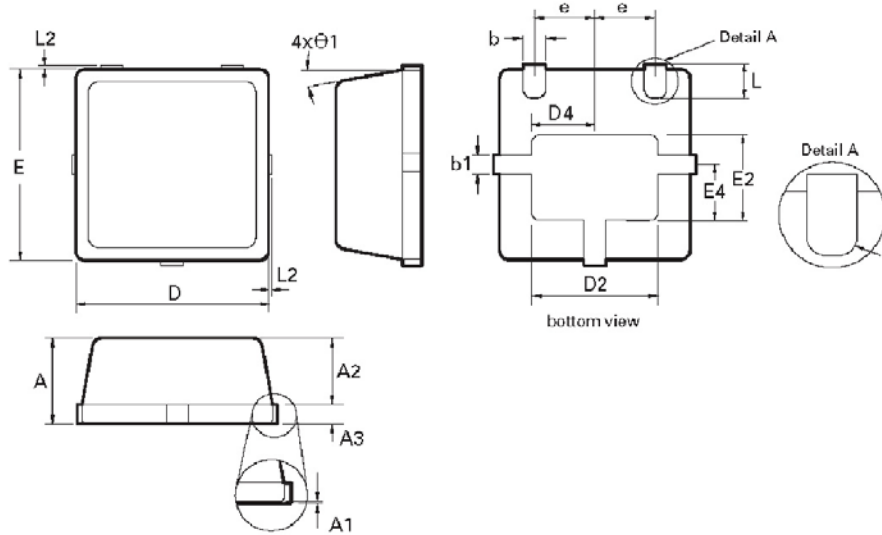
Switching time waveforms



Switching time test circuit

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Package outline - 2mm x 2mm DFN



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.0315	0.0393	0.80	1.00	e	0.0255 REF.		0.65 REF.	
A1	0.00	0.002	0.00	0.05	E	0.0787 BSC		2.00 BSC	
A2	0.0255	0.0295	0.65	0.75	E2	0.031	0.039	0.79	0.99
A3	0.0059	0.0098	0.15	0.25	E4	0.0188	0.0267	0.48	0.68
b	0.0070	0.0110	0.18	0.28	L	0.0078	0.0177	0.20	0.45
b1	0.0066	0.0118	0.17	0.30	L2	0.005 REF.		0.125 MAX.	
D	0.0787 BSC		2.00 BSC		r	0.0029 BSC		0.075 BSC	
D2	0.0480	0.0559	1.22	1.42	θ	0°	12°	0°	12°
D4	0.0220	0.0299	0.56	0.76	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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